

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|--|------------------|---------|------------------|
| L1 | 8 | SiC near3 single adj crystal same gate adj (insulati\$2 or dielectric or oxide or nitride) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/12 19:11 |
| L2 | 1 | SiC near3 single adj crystalline same gate adj (insulati\$2 or dielectric or oxide or nitride) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/12 19:35 |
| S1 | 430 | gate adj (insulation or insulating) same (krypton or kr) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:38 |
| S2 | 10 | S1 and siC near2 (substrate or wafer) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:41 |
| S3 | 10 | S1 and siC near3 (substrate or wafer) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:41 |
| S4 | 10 | S1 and SiC near3 (substrate or wafer) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:43 |
| S5 | 1466 | gate adj (insulation or insulating) same (argon or Ar) | US_PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:44 |

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|-----|-----|---|---|----|-----|---------------------|
| S6 | 36 | S5 and SiC near3 (substrate or wafer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 20:45 |
| S7 | 4 | S5 and SiC near3 (substrate or wafer) same plasma | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 21:17 |
| S8 | 435 | gate adj (insulation or insulating) same (xenon or Xe) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 21:20 |
| S9 | 45 | S8 and SiC | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 21:21 |
| S10 | 45 | S8 and SiC and plasma | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/04 21:21 |
| S14 | 36 | (insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon) same SiC | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/05 07:26 |
| S15 | 466 | gate near2 (insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/05 07:41 |
| S16 | 467 | gate near1 (insulation or insulating) adj (film or layer) same plasma same (Kr or krypton or Ar or argon or Xe or xenon) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/05 07:41 |
| S17 | 1 | ("7226848").PN. | USPAT | OR | OFF | 2008/04/06 13:11 |

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|-----|-----|---|---|----|-----|---------------------|
| S19 | 1 | ("6975018").PN. | USPAT | OR | OFF | 2008/04/06 13:52 |
| S22 | 1 | ("7279066").PN. | USPAT | OR | OFF | 2008/04/06 14:13 |
| S24 | 1 | "4027320".PN. | USPAT; USOCR | OR | OFF | 2008/04/06 14:14 |
| S25 | 1 | "5034086".PN. | USPAT; USOCR | OR | OFF | 2008/04/06 14:15 |
| S26 | 1 | "5889304".PN. | USPAT; USOCR | OR | OFF | 2008/04/06 14:17 |
| S27 | 1 | "6497783".PN. | USPAT; USOCR | OR | OFF | 2008/04/06 14:17 |
| S28 | 1 | "20030003243".PN. | US-PGPUB | OR | OFF | 2008/04/06 14:19 |
| S29 | 7 | SiC near2 substrate same plasma same gate adj (insulation or insulating) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 14:59 |
| S30 | 132 | SiC near2 substrate same gate adj (insulation or insulating) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 15:02 |
| S32 | 10 | (SiC near2 Si)near2 substrate same advantage\$1 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 15:54 |
| S33 | 690 | (SiC near2 Si)near2 substrate | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 15:57 |
| S34 | 525 | (SiC or silicon adj carbide)near2 substrate same plasma | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 17:04 |

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| S35 | 15 | (SiC or silicon adj carbide)near2 substrate same plasma with (insulation or insulating) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 17:05 |
| S36 | 1 | ("6208012").PN. | USPAT | OR | OFF | 2008/04/06 18:41 |
| S37 | 1 | ("6028012").PN. | USPAT | OR | OFF | 2008/04/06 18:42 |
| S38 | 7 | ("4788082" "5562952" "5597744" "5614749" "5656516" "5789311" "5796122").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/04/06 18:42 |
| S39 | 250 | (SiC or silicon adj carbide)near2 substrate same gate adj (insulation or insulating) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/06 18:49 |
| S40 | 9 | (SiC or silicon adj carbide)near2 substrate same gate adj (insulation or insulating) same plasma | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/07 08:38 |
| S43 | 12 | (SiC or silicon adj carbide)near2 substrate same gate near2 (insulation or insulating) same plasma | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/07 08:44 |
| S44 | 1 | ("6399520").PN. | USPAT | OR | OFF | 2008/04/07 09:10 |
| S45 | 1 | ("7122488").PN. | USPAT | OR | OFF | 2008/04/07 10:09 |
| S46 | 7 | ("20030059556" "20040129673" "4888820" "5135885" "6136727" "6437371" "6482704").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/04/07 10:10 |
| S47 | 1 | ("5135885").PN. | USPAT | OR | OFF | 2008/04/07 10:21 |

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|-----|-----|--|---|----|-----|---------------------|
| S48 | 1 | S47 and (argon or Ar) | USPAT | OR | OFF | 2008/04/07 10:21 |
| S51 | 2 | "20040129673" | US-PGPUB; USPAT | OR | OFF | 2008/04/07 10:28 |
| S53 | 1 | ("6975018").PN. | USPAT | OR | OFF | 2008/04/07 10:56 |
| S55 | 431 | gate adj (insulation or insulating) same (krypton or kr) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/04/12 00:12 |
| S56 | 155 | gate adj (insulation or insulating) same (krypton or kr) | USPAT | OR | OFF | 2008/04/12 00:12 |
| S57 | 1 | ("5972801").PN. | USPAT | OR | OFF | 2008/04/12 00:50 |

4/12/08 7:46:53 PM

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